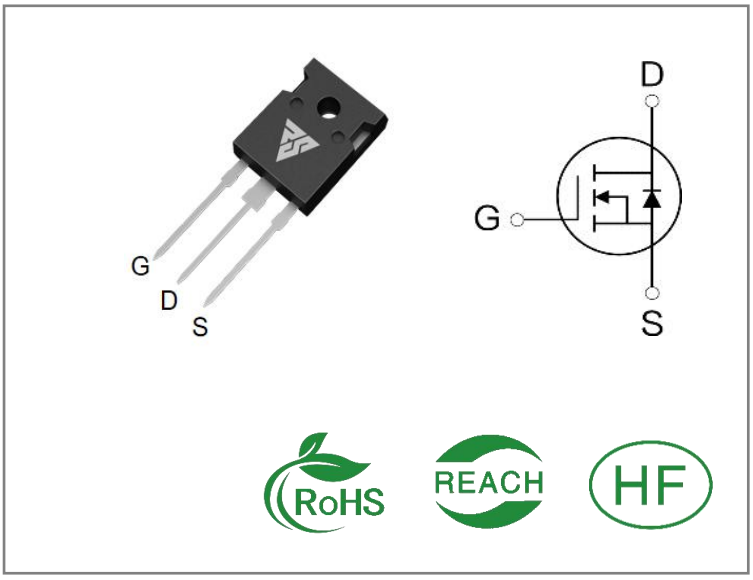
ID	R_{DS}(ON)(Typ)	VDSS
28A	0.14Ω	500V



Applications:
- Switch Mode Power Supply(SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

Features:
- Fast switching speed
- 100% avalanche tested
- Improved dv/dt capability

Ordering Information

Part Number	Package	Marking	Packing	Qty.
RS28N50W	T0-247-3	RS28N50W	Tube	30 PCS

Absolute Maximun Ratings Tc= 2 5℃ unless otherwise specified

Symbol	Parameter	RS28N50W	Units
VDSS	Drain-to-Source Voltage	500	V
ID	Continuous Drain Current TC=25℃	28	A
ID	Continuous Drain Current TC=100℃	15	
IDM	Pulsed Drain Current (Note*1)	112	
PD	Power Dissipation	120	W
VGS	Gate- to- Source Voltage	±30	V
EAS	Single Pulse Avalanche Engergy L = 10mH,,VDD = 50V, RG = 25 Ω	520	mJ
TL TPKG	Maximum Temperature for Soldering	300 260	℃
	Leads at 0.063in(1.6mm)from Case for 10 seconds Package Body for 10 seconds		
TJ and TSTG	Operating Junction and Storage Temperature Range	-55 to 150	

* Drain Current Limited by Maximum Junction Temperature
Caution: Stresses greater than those listed in the“ Absolute Maximum Ratings” Table may cause permanent damage to the device.

Thermal Resistance

Symbol	Parameter	RS28N50W	Units	Test Conditions
RθJC	Junction-to-Case	0.29	℃/ W	Drain lead soldered to water cooled heatsink, PD adjusted for a peak junction temperature of + 1 5 0 ℃
RθJA	Junction-to-Ambient	62		1 cubic foot chamber,free air.

OFF Characteristics TJ= 25℃ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BVDSS	Drain- to- source Breakdown Voltage	500	--	--	V	VGS=0V,ID=250μA
IDSS	Drain- to- Source Leakage Current	--	--	1	μA	VDS=500V,VGS=0V
IGSS	Gate- to- Source Forward Leakage	--	--	100	nA	VGS=30V ,VDS=0V
	Gate- to- Source Reverse Leakage	--	--	-100		VGS=-30V ,VDS=0V

ON Characteristics TJ=25℃ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
RDS(on)	Static Drain- to- Source On-Resistance(Note*2)	--	0.14	0.18	Ω	VGS=10V,ID=14A
VGS(TH)	Gate Threshold Voltage	3	--	4	V	VGS=VDS,ID=250μA

Resistive Switching Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
td(ON)	Turn- on Delay Time	--	66	--	nS	VDS=250V ID=28A RG=25Ω
trise	Rise Time	--	59	--		
td(OFF)	Turn- OFF Delay Time	--	427	--		
tfall	Fall Time	--	108	--		

Dynamic Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
Ciss	Input Capacitance	--	4295	--	pF	VGS=0V VDS=25V f=1.0MHz
Coss	Output Capacitance	--	450	--		
Crss	Reverse Transfer Capacitance	--	32	--		
Qg	Total Gate Charge	--	22	--	nC	VDS=400V ID=28A VGS=10V
Qgs	Gate- to- Source Charge	--	4	--		
Qgd	Gate-to-Drain(" Miller") Charge	--	13	--		

Source- Drain Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
IS	Continuous Source Current	--	--	28	A	Integral pn- diode in MOSFET
ISM	Maximum Pulsed Current	--	--	112	A	
VSD	Diode Forward Voltage	--	--	1.4	V	IS=14A,VGS=0V
trr	Reverse Recovery Time	--	482	--	nS	VGS=0V IS=14A,di/dt=100 A/μs
Qrr	Reverse Recovery Charge	--	7.6	--	μC	

Notes:

* 1. Repetitive rating, pulse width limited by maximum junction temperature.
* 2. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 1%

Typical Feature Curve

Figure 1. Output Characteristics (T_J = 25°C)

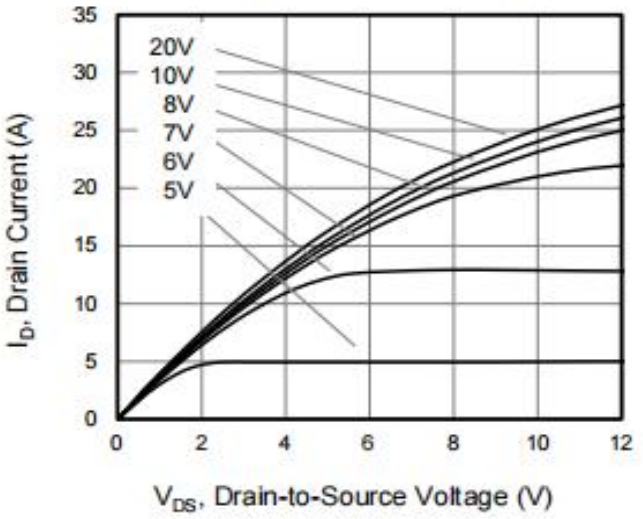


Figure 2. Body Diode Forward Voltage

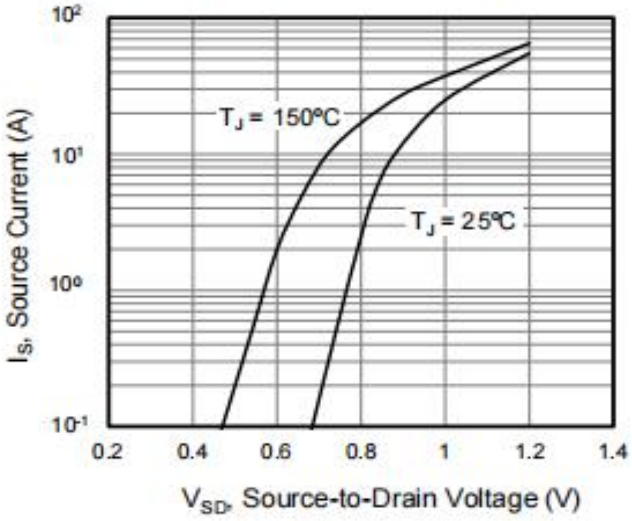


Figure 3. Drain Current vs. Temperature

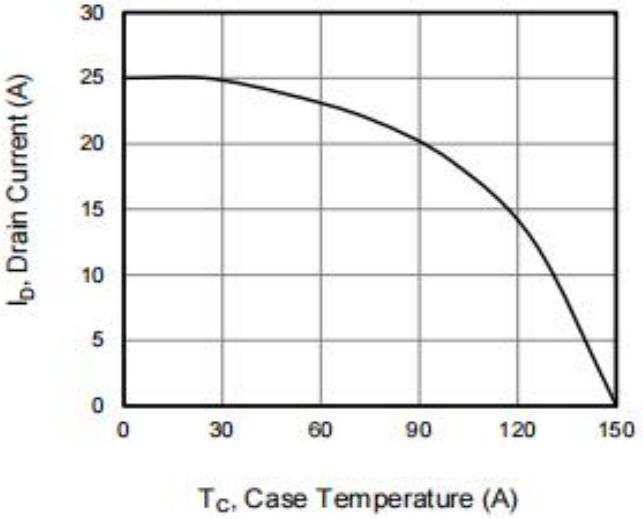


Figure 4. BV_{DSS} Variation vs. Temperature

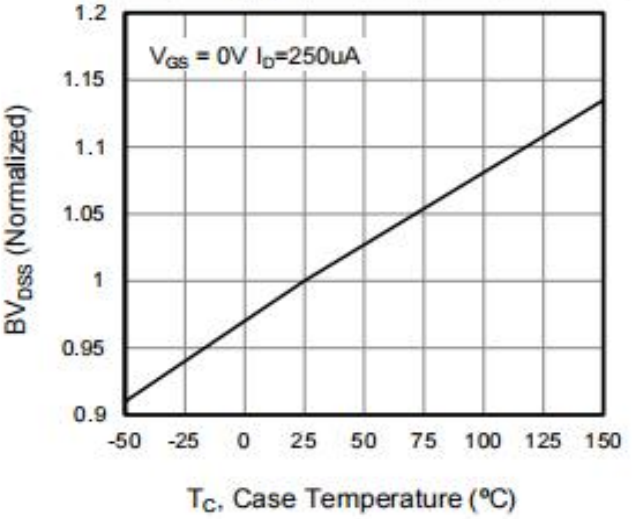


Figure 5. Transfer Characteristics

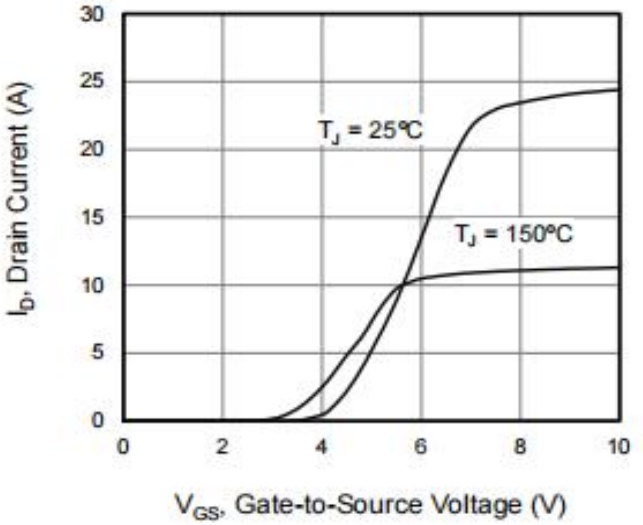


Figure 6. On-Resistance vs. Temperature

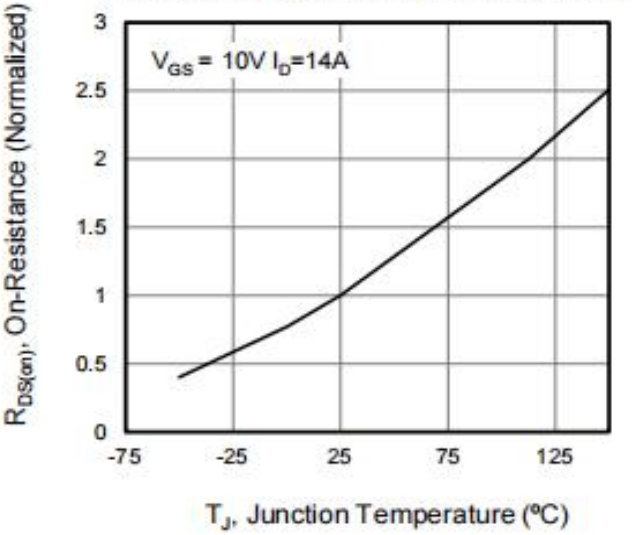


Figure 7. Capacitance

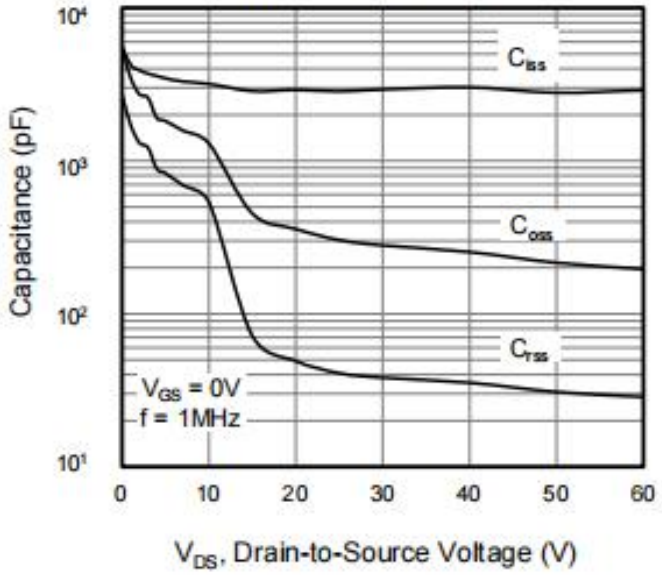


Figure 8. Gate Charge

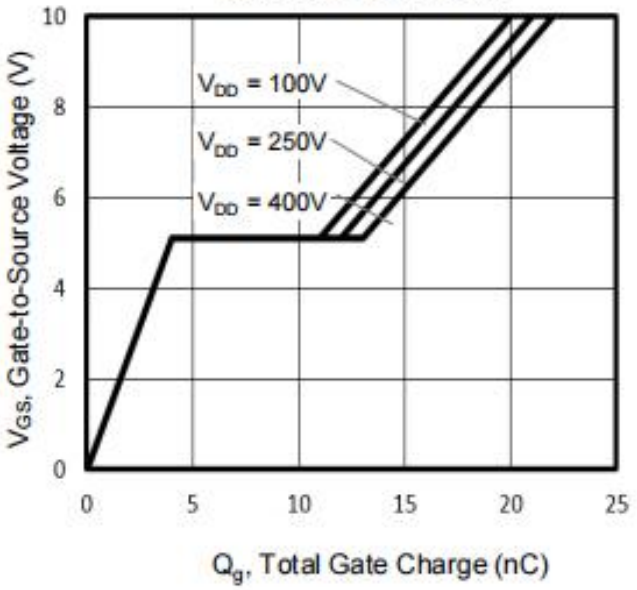
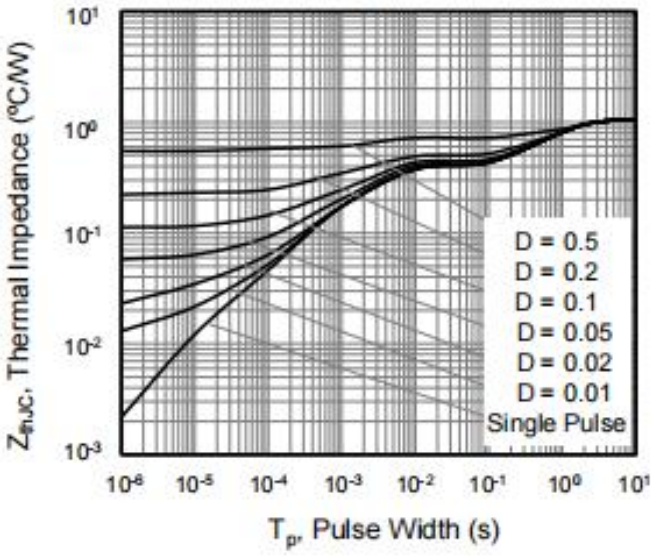


Figure 9. Transient Thermal Impedance

TO-247/TO-3P



Test Circuits and Waveforms

Figure A: Gate Charge Test Circuit and Waveform

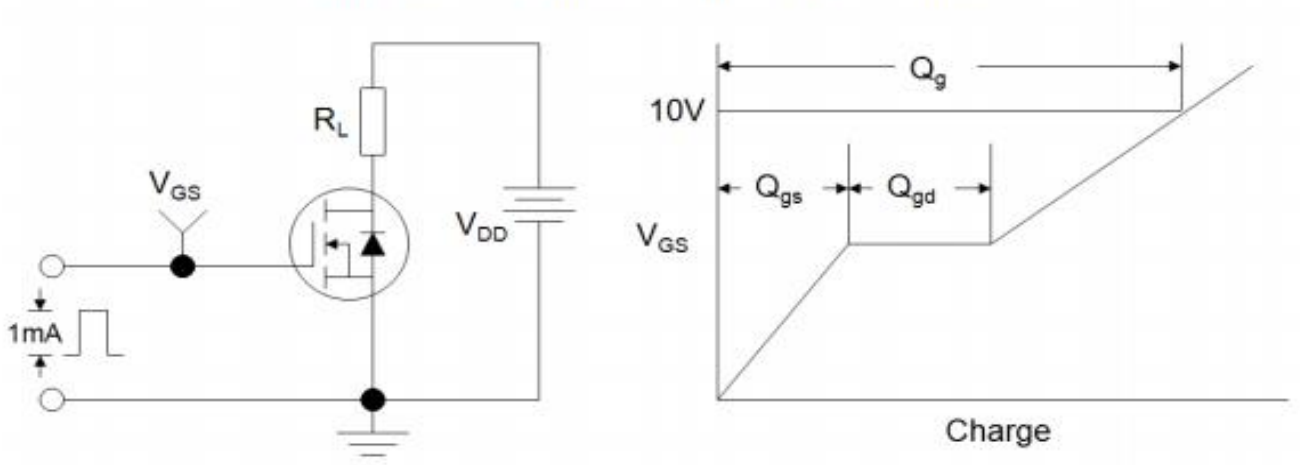


Figure B: Resistive Switching Test Circuit and Waveform

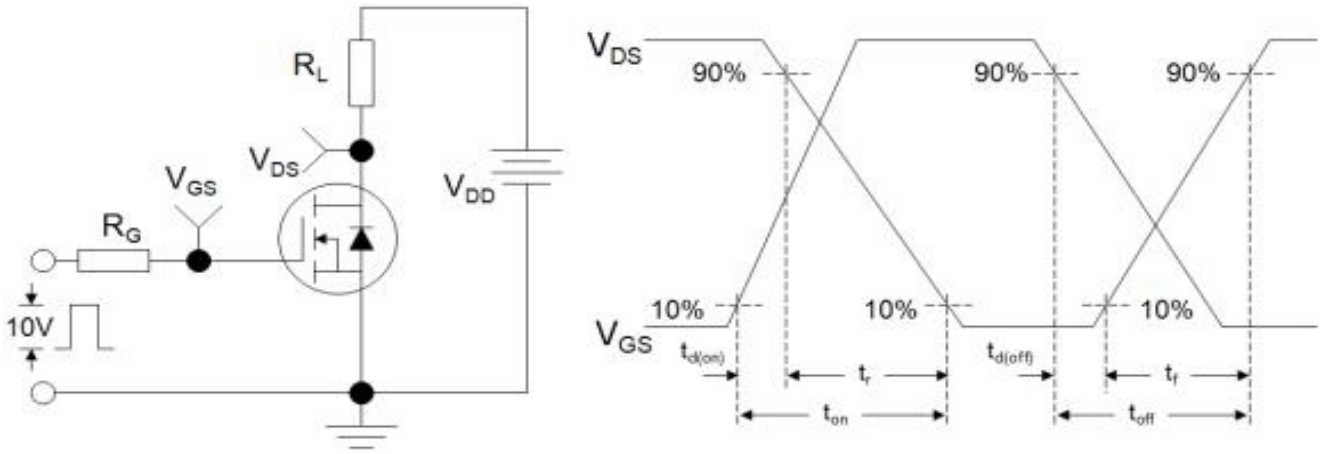
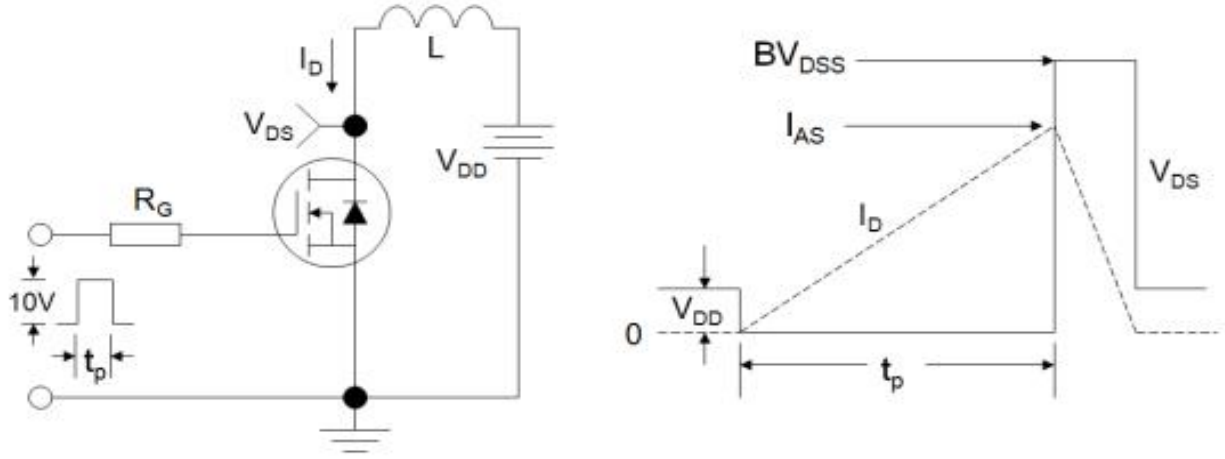
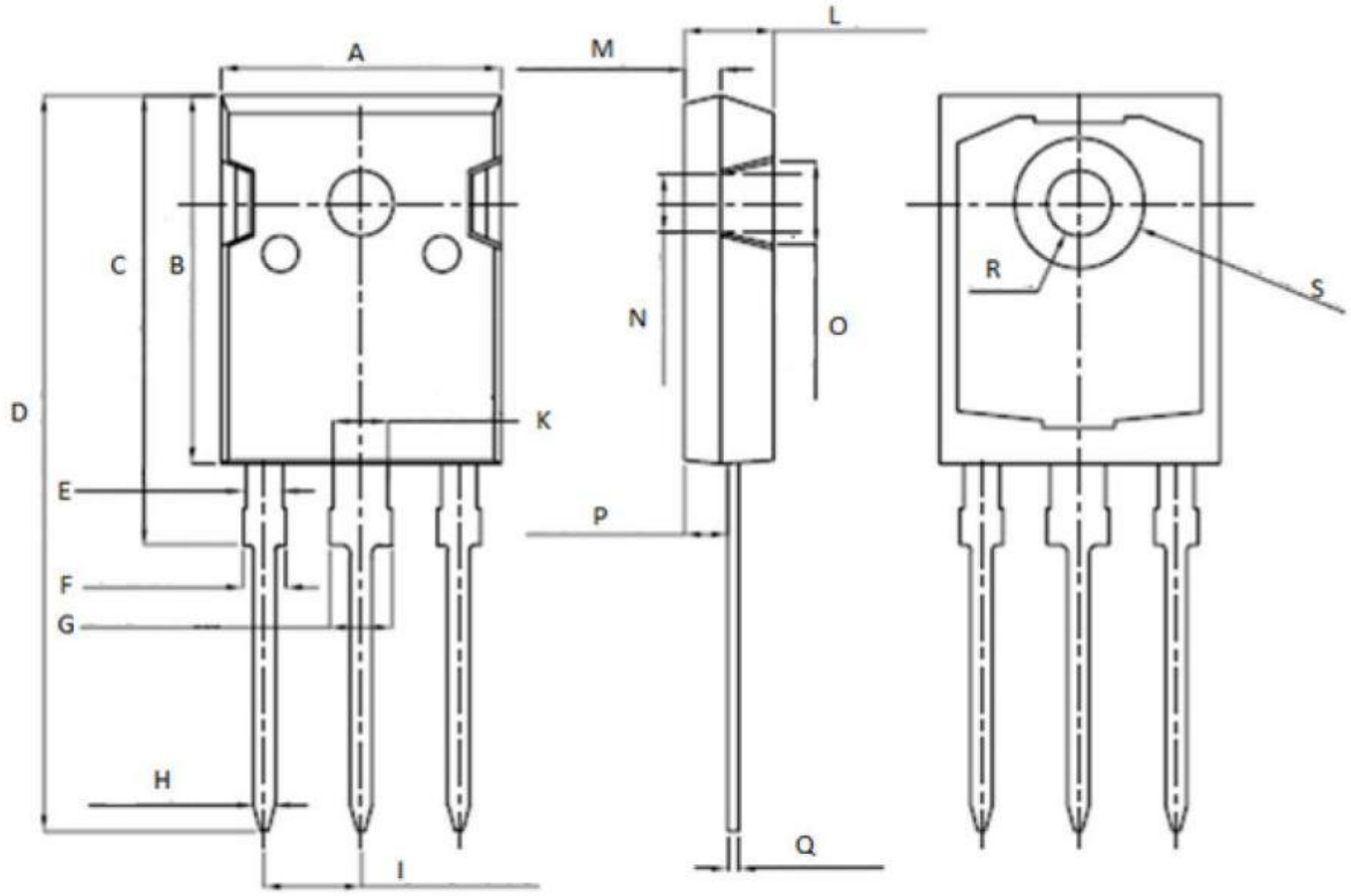


Figure C: Unclamped Inductive Switching Test Circuit and Waveform



Package outline drawing(TO-247 Unit: mm)



Unit: mm		
Symbol	Min.	Max.
A	15.95	16.25
B	20.85	21.25
C	20.95	21.35
D	40.5	40.9
E	1.9	2.1
F	2.1	2.25
G	3.1	3.25
H	1.1	1.3
I	5.40	5.50

Unit: mm		
Symbol	Min.	Max.
K	2.90	3.10
L	4.90	5.30
M	1.90	2.10
N	4.50	4.70
O	5.40	5.60
P	2.29	2.49
Q	0.51	0.71
R	ϕ3.5	ϕ3.7
S	ϕ7.1	ϕ7.3

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